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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	56340
Total RAM Bits	1869824
Number of I/O	267
Number of Gates	-
Voltage - Supply	1.14V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	-55°C ~ 125°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m2gl050t-1fgg484m

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4.3.2 Theta-JA

Junction-to-ambient thermal resistance (θ_{JA}) is determined under standard conditions specified by JEDEC (JESD-51), but it has little relevance in actual performance of the product. It must be used with caution, but it is useful for comparing the thermal performance of one package to another.

The maximum power dissipation allowed is calculated using EQ 4.

$$\text{Maximum Power Allowed} = \frac{T_{J(MAX)} - T_{A(MAX)}}{\theta_{JA}}$$

EQ 4

The absolute maximum junction temperature is 100°C. EQ 5 shows a sample calculation of the absolute maximum power dissipation allowed for the M2GL050-FG484 package at Military temperature and in still air, where:

θ_{JA} = 15.29°C/W (taken from Table 7 on page 15)

T_A = 85°C

$$\text{Maximum Power Allowed} = \frac{100°C - 85°C}{15.29°C/W} = 0.981\ W$$

EQ 5

The power consumption of a device can be calculated using the Microsemi SoC Products Group power calculator. The device's power consumption must be lower than the calculated maximum power dissipation by the package.

If the power consumption is higher than the device's maximum allowable power dissipation, a heat sink can be attached on top of the case, or the airflow inside the system must be increased.

4.3.3 Theta-JB

Junction-to-board thermal resistance (θ_{JB}) measures the ability of the package to dissipate heat from the surface of the chip to the PCB. As defined by the JEDEC (JESD-51) standard, the thermal resistance from junction to board uses an isothermal ring cold plate zone concept. The ring cold plate is simply a means to generate an isothermal boundary condition at the perimeter. The cold plate is mounted on a JEDEC standard board with a minimum distance of 5.0 mm away from the package edge.

4.3.4 Theta-JC

Junction-to-case thermal resistance (θ_{JC}) measures the ability of a device to dissipate heat from the surface of the chip to the top or bottom surface of the package. It is applicable for packages used with external heat sinks. Constant temperature is applied to the surface in consideration and acts as a boundary condition.

This only applies to situations where all or nearly all of the heat is dissipated through the surface in consideration.

8.3. Tristate Buffer and AC Loading

The tristate path for enable path loadings is described in the respective specifications. The methodology of characterization is illustrated by the enable path test point shown in Figure 4.

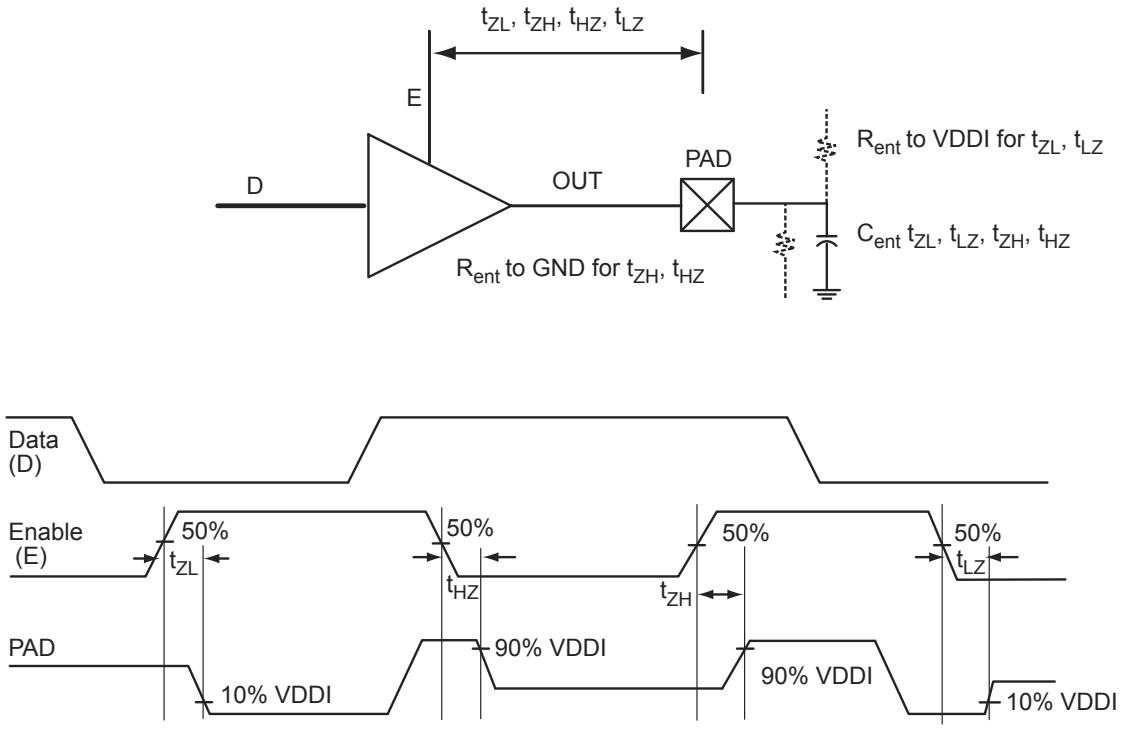

***Figure 4* • Tristate Buffer for Enable Path Test Point**

8.6.3 2.5 V LVCMOS

LVCMOS 2.5 V is a general standard for 2.5 V applications and is supported in IGLOO2 FPGA and SmartFusion2 SoC FPGAs in compliance to the JEDEC specification JESD8-5A.

8.6.3.1 Minimum and Maximum AC/DC Input and Output Levels Specification

Table 27 • LVCMOS 2.5 V DC Voltage Specification

Symbol	Parameters	Conditions	Min	Typ	Max	Units	Notes
LVCMOS 2.5 V Recommended DC Operating Conditions							
VDDI	Supply voltage		2.375	2.5	2.625	V	–
LVCMOS 2.5 V DC Input Voltage Specification							
VIH (DC)	DC input logic High (for MSIOD and DDRIO I/O Bank)		1.7	–	2.625	V	–
VIH (DC)	DC input logic High (for MSIO I/O Bank)		1.7	–	2.75	V	–
VIL (DC)	DC input logic Low		–0.3	–	0.7	V	–
IIH (DC)	Input current High		–	–	10	µA	–
IIL (DC)	Input current Low		–	–	10	µA	–
LVCMOS 2.5 V DC Output Voltage Specification							
VOH	DC output logic High		1.7	–	–	V	*
VOL	DC output logic Low		–	–	0.7	V	*
*Note: * The VOH/VOL test points selected ensure compliance with LVCMOS 2.5 V JEDEC8-5A requirements.*							

Table 28 • LVCMOS 2.5 V Maximum AC Switching Speeds

Symbol	Parameters	Conditions	Min	Typ	Max	Units
Dmax	Maximum data rate (for DDRIO I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	360	Mbps
Dmax	Maximum data rate (for MSIO I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	360	Mbps
Dmax	Maximum data rate (for MSIOD I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	370	Mbps

Table 29 • LVCMOS 2.5 V AC Test Parameters and Driver Impedance Specifications

Symbols	Parameters	Conditions	Min	Typ	Max	Units
LVCMOS 2.5 V Calibrated Impedance Option						
Rodt_cal	Supported output driver calibrated impedance (for DDRIO I/O Bank)	–	–	75, 60, 50, 33, 25, 20	–	Ω
LVCMOS 2.5 V AC Test Parameters Specifications						
Vtrip	Measuring/trip point for data path	–	–	1.2	–	V
Rent	Resistance for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})	–	–	2k	–	Ω
Cent	Capacitive loading for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})	–	–	5	–	pF
Cload	Capacitive loading for data path (t_{DP})	–	–	5	–	pF

Table 46 • **LVCMOS 1.2 V Minimum and Maximum DC Input and Output Levels**

IIL (DC)	Input current Low		–	–	10	µA
LVCMOS 1.2 V DC Output Voltage Specification						
VOH	DC output logic High	–	VDDI × 0.75	–	–	V
VOL	DC output logic Low	–	–	–	VDDI × 0.25	V

Table 47 • **LVCMOS 1.2 V Maximum AC Switching Speeds**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
LVCMOS 1.2 V Maximum AC Switching Speed						
Dmax	Maximum data rate (for DDRIO I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	180	Mbps
Dmax	Maximum data rate (for MSIO I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	100	Mbps
Dmax	Maximum data rate (for MSIOD I/O Bank)	AC loading: 17 pF load, maximum drive/slew	–	–	140	Mbps

Table 48 • **LVCMOS 1.2 V AC Calibrated Impedance and Test Parameters Specifications**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
LVCMOS 1.2 V AC Calibrated Impedance Option						
Rodt_cal	Supported output driver calibrated impedance (for DDRIO I/O Bank)		–	75, 60, 50, 40	–	Ω
LVCMOS 1.2 V AC Test Parameters Specifications						
Vtrip	Measuring/trip point for data path		–	0.6	–	V
Rent	Resistance for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	2k	–	Ω
Cent	Capacitive loading for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	5	–	pF
Cload	Capacitive loading for data path (t_{DP})		–	5	–	pF

Table 49 • **LVCMOS 1.2 V Transmitter Drive Strength Specifications**

Output Drive Selection			VOH (V)	VOL (V)		
MSIO I/O Bank	MSIOD I/O Bank	DDRIO I/O Bank (with Fixed Code)	Min	Max	IOH (at VOH) mA	IOL (at VOL) mA
2 mA	2 mA	2 mA	VDDI × 0.75	VDDI × 0.25	2	2
4 mA	4 mA	4 mA	VDDI × 0.75	VDDI × 0.25	4	4
N/A	N/A	6 mA	VDDI × 0.75	VDDI × 0.25	6	6

8.6.7.2 AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 54 • **PCI/PCIX AC Switching Characteristics for Receiver (Input Buffers)**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI = 3.15 V

	ODT (On Die Termination)	Speed Grade –1		Units
		t_{PY}	t_{PYS}	
PCI/PCIX (for MSIO I/O Bank)	None	2.379	2.387	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 55 • **PCI/PCIX AC Switching Characteristics for Transmitter (Output and Tristate Buffers)**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI= 3.15 V

	Speed Grade –1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
PCI/PCIX (for MSIO I/O Bank)	2.394	2.274	2.316	6.876	6.242	ns

8.7 Memory Interface and Voltage Referenced I/O Standards

8.7.1 High-Speed Transceiver Logic (HSTL)

The High-Speed Transceiver Logic (HSTL) standard is a general purpose high-speed bus standard sponsored by IBM (EIA/JESD8-6). IGLOO2 FPGA and SmartFusion2 SoC FPGA devices support two classes of the 1.5 V HSTL. These differential versions of the standard require a differential amplifier input buffer and a push-pull output buffer.

8.7.1.1 Minimum and Maximum Input and Output Levels Specification

Table 56 • **HSTL DC Voltage Specification (Applicable to DDRIO I/O Bank Only)**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
HSTL Recommended DC Operating Conditions						
VDDI	Supply voltage		1.425	1.5	1.575	V
VTT	Termination voltage		0.698	0.750	0.803	V
VREF	Input reference voltage		0.698	0.750	0.803	V
HSTL DC Input Voltage Specification						
VIH (DC)	DC input logic High		VREF + 0.1	–	1.575	V
VIL (DC)	DC input logic Low		–0.3	–	VREF – 0.1	V
IIH (DC)	Input current High		–	–	10	µA
IIL (DC)	Input current Low		–	–	10	µA
HSTL DC Output Voltage Specification						
HSTL Class I						
VOH	DC output logic High		VDDI – 0.4	–	–	V
VOL	DC output logic Low		–	–	0.4	V
IOH at VOH	Output minimum source DC current		–7.0	–	–	mA
IOL at VOL	Output minimum sink current		7.0	–	–	mA
HSTL Class II						
VOH	DC output logic High		VDDI – 0.4	–	–	V

Table 60 • **DDR1/SSTL2 Minimum and Maximum DC Input and Output Levels (continued)**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
IOL at VOL	Output minimum sink current		–8.1	–	–	mA
SSTL2 Class II (DDR Full Drive) – Applicable to MSIO and DDRIO I/O Banks Only						
VOH	DC output logic High		VTT + 0.81	–	–	V
VOL	DC output logic Low		–	–	VTT – 0.81	V
IOH at VOH	Output minimum source DC current		16.2	–	–	mA
IOL at VOL	Output minimum sink current		–16.2	–	–	mA
SSTL2 DC Differential Voltage Specification						
VID (DC)	DC input differential voltage		0.3	–	–	V

Table 61 • **DDR1/SSTL2 AC Specifications**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
SSTL2 Maximum AC Switching Speeds						
Dmax	Maximum data rate (for DDRIO I/O Bank)	AC loading: per JEDEC specifications	–	–	360	Mbps
Dmax	Maximum data rate (for MSIO I/O Bank)	AC loading: 17pF load	–	–	450	Mbps
Dmax	Maximum data rate (for MSIOD I/O Bank)	AC loading: 17pF load	–	–	480	Mbps
SSTL2 AC Differential Voltage Specifications						
VDIFF	AC Input Differential Voltage		0.7	–	–	V
Vx	AC Differential Cross Point Voltage		0.5 × VDDI - 0.2	–	0.5 × VDDI + 0.2	V
SSTL2 Impedance Specifications						
	Supported output driver calibrated impedance (for DDRIO I/O Bank)	Reference resistor = 150 Ω	–	20, 42	–	Ω
SSTL2 AC Test Parameters Specifications						
Vtrip	Measuring/trip point for data path		–	1.25	–	V
Rent	Resistance for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	2k	–	Ω
Cent	Capacitive loading for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	5	–	pF
Rtt_test	Reference resistance for data test path for SSTL2 Class I (t_{DP})		–	50	–	Ω
Rtt_test	Reference resistance for data test path for SSTL2 Class II (t_{DP})		–	25	–	Ω
Cload	Capacitive loading for data path (t_{DP})		–	5	–	pF

Table 72 • **LPDDR AC/DC Specifications (for DDRIO IO Bank Only)**

LPDDR Reduced Drive						
VOH	DC output logic High	0.9 × VDDI	–	–	V	–
VOL	DC output logic Low	–	–	0.1 × VDDI	V	–
IOH at VOH	Output minimum source DC current	0.1	–	–	mA	–
IOL at VOL	Output minimum sink current	–0.1	–	–	mA	–
LPDDR Full Drive						*
VOH	DC output logic High	0.9 × VDDI	–	–	V	–
VOL	DC output logic Low	–	–	0.1 × VDDI	V	–
IOH at VOH	Output minimum source DC current	0.1	–	–	mA	–
IOL at VOL	Output minimum sink current	–0.1	–	–	mA	–
LPDDR DC Differential Voltage Specification						
VID (DC)	DC input differential voltage	0.4 × VDDI	–	–	V	–
*Note: *To meet JEDEC Electrical Compliance, use LPDDR Full Drive Transmitter.*						

Table 73 • **LPDDR Maximum AC Switching Speeds (for DDRIO I/O Bank Only)**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
Dmax	Maximum data rate	AC loading: per JEDEC specifications	–	–	360	Mbps

Table 74 • **LPDDR AC Specifications (for DDRIO IO Bank Only)**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
LPDDR AC Differential Voltage Specification						
VDIFF (AC)	AC Input differential voltage	–	0.6 × VDDI	–	–	V
Vx (AC)	AC Differential Cross Point Voltage	–	0.4 × VDDI	–	0.6 × VDDI	V
LPDDR Impedance Specifications						
Rref	Supported Output Driver Calibrated Impedance	Reference Resistor = 150 Ω	–	20,42	–	Ω
RTT	Effective impedance Value - ODT	Reference Resistor = 150 Ω	–	50, 75, 150	–	Ω
LPDDR AC Test Parameters Specifications						
Vtrip	Measuring/Trip Point for Data Path	–	–	0.9	–	V
Rent	Resistance for Enable Path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})	–	–	2k	–	Ω
Cent	Capacitive Loading for Enable Path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})	–	–	5	–	pF
Rtt_test	Reference resistance for Data Test Path for LPDDR ($t_{DP)}$	–	–	50	–	Ω
Cload	Capacitive Loading for Data Path (t_{DP})	–	–	5	–	pF

8.8. Differential I/O Standards

Configuration of the I/O modules as a differential pair is handled by Microsemi SoC Products Group Libero® System-on-Chip (SoC) software when the user instantiates a differential I/O macro in the design. Differential I/Os can also be used in conjunction with the embedded Input register (InReg), Output register (OutReg), Enable register (EnReg), and Double Data Rate registers (DDR).

8.8.1 LVDS

Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard.

8.8.1.1 Minimum and Maximum Input and Output Levels

Table 83 • **LVDS DC Voltage Specification**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
LVDS Recommended DC Operating Conditions						
VDDI	Supply voltage	2.5 V range	2.375	2.5	2.625	V
VDDI	Supply voltage	3.3 V range	3.15	3.3	3.45	V
LVDS DC Input Voltage Specification						
VI	DC Input voltage	2.5 V range	0	–	2.925	V
VI	DC input voltage	3.3 V range	0	–	3.45	V
IIH (DC)	Input current High		–	–	10	µA
IIL (DC)	Input current Low		–	–	10	µA
LVDS DC Output Voltage Specification						
VOH	DC output logic High		1.25	1.425	1.6	V
VOL	DC output logic Low		0.9	1.075	1.25	V
LVDS Differential Voltage Specification						
VOD	Differential output voltage swing		250	350	450	mV
VOCM	Output common mode voltage		1.125	1.25	1.375	V
VICM	Input common mode voltage		0.05	1.25	2.35	V
VID	Input differential voltage		100	350	600	mV

Table 84 • **LVDS AC Specifications**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
LVDS Maximum AC Switching Speed						
Dmax	Maximum data rate (for MSIO I/O Bank)	AC loading: 12 pF / 100 Ω differential load	–	–	480	Mbps
Dmax	Maximum data rate (for MSIOD I/O Bank)	AC loading: 10 pF / 100 Ω differential load	–	–	480	Mbps
LVDS Impedance Specification						
Rt	Termination resistance	–	–	100	–	Ω
LVDS AC Test Parameters Specifications						
Vtrip	Measuring/trip point for data path		–	Cross point	–	V
Rent	Resistance for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	2k	–	Ω
Cent	Capacitive loading for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	5	–	pF

8.8.1.2 LVDS25 AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 85 • LVDS25 Receiver Characteristics
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI = 2.375 V

	On-Die Termination (ODT)	Speed Grade –1	Units
		t_{PY}	
LVDS (for MSIO I/O Bank)	None	3.061	ns
	100	3.057	ns
LVDS (for MSIOD I/O Bank)	None	2.792	ns
	100	2.787	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 86 • LVDS25 Transmitter Characteristics
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI = 2.375 V

	Speed Grade –1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
LVDS (for MSIO I/O Bank)	2.299	2.602	2.589	2.305	2.32	ns
LVDS (for MSIOD I/O Bank)						
No pre-emphasis	1.656	1.845	1.838	1.992	1.969	ns
Min pre-emphasis	1.583	1.868	1.866	2.018	1.998	ns
Med pre-emphasis	1.559	1.893	1.886	2.045	2.021	ns

8.8.1.3 LVDS33 AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 87 • LVDS33 Receiver Characteristics
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI = 3.15 V

	On Die Termination (ODT)	Speed Grade –1	Units
		t_{PY}	
LVDS33 (for MSIO I/O Bank)	None	2.763	ns
	100	2.76	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 88 • LVDS33 Transmitter Characteristics
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI = 3.15 V

	Speed Grade –1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
LVDS33 (for MSIO I/O Bank)	2.069	2.112	2.106	2.078	2.09	ns

8.8.2 B-LVDS

Bus LVDS (B-LVDS) specifications extend the existing LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers.

8.8.2.1 Minimum and Maximum AC/DC Input and Output Levels Specification

Table 89 • **B-LVDS DC Voltage Specification**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
Bus-LVDS Recommended DC Operating Conditions						
VDDI	Supply voltage		2.375	2.5	2.625	V
Bus-LVDS DC Input Voltage Specification						
VI	DC input voltage		0	–	2.925	V
IIH (DC)	Input current High		–	–	10	µA
IIL (DC)	Input current Low		–	–	10	µA
Bus-LVDS DC Output Voltage Specification (for MSIO I/O Bank only)						
VOH	DC output logic High		1.25	1.425	1.6	V
VOL	DC output logic Low		0.9	1.075	1.25	V
Bus-LVDS Differential Voltage Specification						
VOD	Differential output voltage swing (for MSIO I/O Bank only)		65	–	460	mV
VOCM	Output common mode voltage (for MSIO I/O Bank only)		1.1	–	1.5	V
VICM	Input common mode voltage		0.05	–	2.4	V
VID	Input differential voltage		0.1	–	VDDI	V

Table 90 • **B-LVDS AC Specifications**

Symbols	Parameters	Conditions	Min	Typ	Max	Units
Bus-LVDS Maximum AC Switching Speed						
Dmax	Maximum data rate (for MSIO I/O Bank)	AC loading: 2 pF / 100 Ω differential load	–	–	450	Mbps
Bus-LVDS Impedance Specifications						
Rt	Termination resistance		–	27	–	Ω
Bus-LVDS AC Test Parameters Specifications						
Vtrip	Measuring/trip point for data path		–	Cross point	–	V
Rent	Resistance for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	2k	–	Ω
Cent	Capacitive loading for enable path (t_{ZH}, t_{ZL}, t_{HZ}, t_{LZ})		–	5	–	pF

8.8.4.2 AC Switching Characteristics

AC Switching Characteristics for Receiver (Input Buffers)

Table 99 • Mini-LVDS AC Switching Characteristics for Receiver (Input Buffers)
Worst-case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI= 2.375 V

	On-Die Termination (ODT)	Speed Grade –1	Units
		t_{PY}	
Mini-LVDS (for MSIO I/O Bank)	None	3.112	ns
	100	2.995	ns
Mini-LVDS (for MSIOD I/O Bank)	None	2.612	ns
	100	2.612	ns

AC Switching Characteristics for Transmitter (Output and Tristate Buffers)

Table 100 • Mini-LVDS AC Switching Characteristics for Transmitter (Output and Tristate Buffers)
Worst-case Military Conditions: T_J = 125°C, VDD = 1.14 V, VDDI= 2.375 V

	Speed Grade –1					Units
	t_{DP}	t_{ZL}	t_{ZH}	t_{HZ}	t_{LZ}	
Mini-LVDS (for MSIO I/O Bank)	2.3	2.602	2.59	2.306	2.32	ns
Mini-LVDS (for MSIOD I/O Bank)						
No pre-emphasis	1.652	1.84	1.833	1.988	1.965	ns
Min pre-emphasis	1.652	1.84	1.833	1.988	1.965	ns
Med pre-emphasis	1.577	1.868	1.86	2.02	1.994	ns
Max pre-emphasis	1.555	1.894	1.883	2.048	2.019	ns

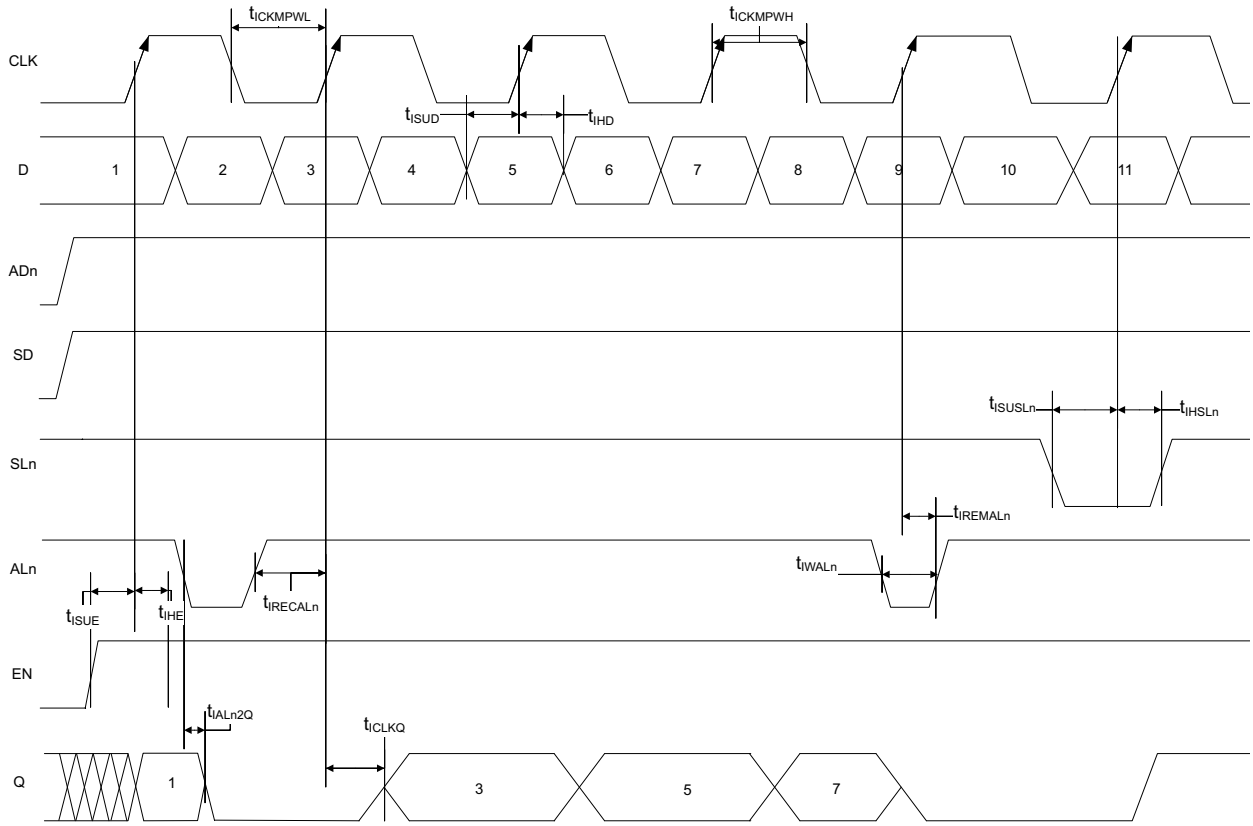

***Figure 6* • I/O Register Input Timing Diagram**

***Table 108* • Input Data Register Propagation Delays**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Measuring Nodes (from, to)*	Speed Grade –1	Units
t_{IBYP}	Bypass Delay of the Input Register	F,G	0.364	ns
t_{ICLKQ}	Clock-to-Q of the Input Register	E,G	0.165	ns
t_{ISUD}	Data Setup Time for the Input Register	A,E	0.369	ns
t_{IHD}	Data Hold Time for the Input Register	A,E	0	ns
t_{ISUE}	Enable Setup Time for the Input Register	B,E	0.475	ns
t_{IHE}	Enable Hold Time for the Input Register	B,E	0	ns
t_{ISUSL}	Synchronous Load Setup Time for the Input Register	D,E	0.475	ns
t_{IHSL}	Synchronous Load Hold Time for the Input Register	D,E	0	ns
t_{IALn2Q}	Asynchronous Clear-to-Q of the Input Register (ADn=1)	C,G	0.648	ns
	Asynchronous Preset-to-Q of the Input Register (ADn=0)	C,G	0.606	ns

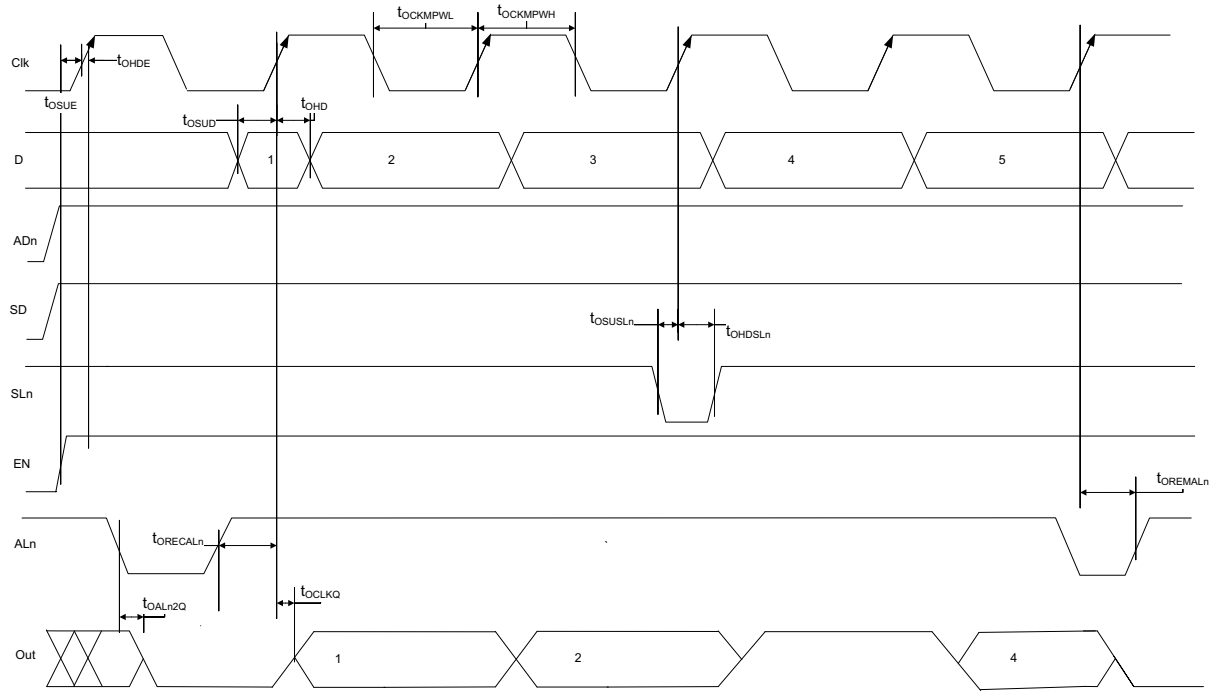

***Figure 8* • I/O Register Output Timing Diagram**

***Table 109* • Output/Enable Data Register Propagation Delays**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Measuring Nodes (from, to)*	Speed Grade –1	Units
tOBYP	Bypass Delay of the Output/Enable Register	F,G or H,I	0.364	ns
tOCLKQ	Clock-to-Q of the Output/Enable Register	E,G or E,I	0.272	ns
tOSUD	Data Setup Time for the Output/Enable Register	A,E or J,E	0.196	ns
tOHD	Data Hold Time for the Output/Enable Register	A,E or J,E	0	ns
tOSUE	Enable Setup Time for the Output/Enable Register	B,E	0.433	ns
tOHE	Enable Hold Time for the Output/Enable Register	B,E	0	ns
tOSUSL	Synchronous Load Setup Time for the Output/Enable Register	D,E	0.203	ns
tOHSL	Synchronous Load Hold Time for the Output/Enable Register	D,E	0	ns
tOALn2Q	Asynchronous Clear-to-Q of the Output/Enable Register (ADn=1)	C,G or C,I	0.523	ns
	Asynchronous Preset-to-Q of the Output/Enable Register (ADn=0)	C,G or C,I	0.545	ns
tOREMALn	Asynchronous Load Removal Time for the Output/Enable Register	C,E	0	ns

9.2.1 Timing Characteristics

Table 113 • **Register Delays**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Speed Grade –1	Units
tCLKQ	Clock-to-Q of the Core Register	0.112	ns
tSUD	Data Setup Time for the Core Register	0.262	ns
tHD	Data Hold Time for the Core Register	0	ns
tSUE	Enable Setup Time for the Core Register	0.346	ns
tHE	Enable Hold Time for the Core Register	0	ns
tSUSL	Synchronous Load Setup Time for the Core Register	0.346	ns
tHSL	Synchronous Load Hold Time for the Core Register	0	ns
tALn2Q	Asynchronous Clear-to-Q of the Core Register (ADn=1)	0.49	ns
	Asynchronous Preset-to-Q of the Core Register (ADn=0)	0.466	ns
tREMALn	Asynchronous Load Removal Time for the Core Register	0	ns
tRECALn	Asynchronous Load Recovery Time for the Core Register	0.364	ns
tWALn	Asynchronous Load Minimum Pulse Width for the Core Register	0.266	ns
tCKMPWH	Clock Minimum Pulse Width High for the Core Register	0.065	ns
tCKMPWL	Clock Minimum Pulse Width Low for the Core Register	0.139	ns

10. Global Resource Characteristics

The IGLOO2 and SmartFusion2 SoC FPGA devices offer a powerful, low skew global routing network which provides an effective clock distribution throughout the FPGA fabric. Refer to the *UG0445: IGLOO2 FPGA and SmartFusion2 SoC FPGA Fabric User Guide* for the positions of various global routing resources. .

Table 114 • **M2S150T Device Global Resource**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Speed Grade –1		Units
		Min	Max	
tRCKL	Input Low Delay for Global Clock	0.788	0.868	ns
tRCKH	Input High Delay for Global Clock	1.46	1.594	ns
tRCKSW	Maximum Skew for Global Clock	–	0.134	ns

Table 115 • **M2S090T Device Global Resource**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Speed Grade –1		Units
		Min	Max	
tRCKL	Input Low Delay for Global Clock	0.793	0.847	ns

Table 119 • RAM1K18 – Dual-Port Mode for Depth × Width Configuration 1Kx18
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V (continued)

Parameter	Description	Speed Grade –1		Units
		Min	Max	
tsrstsu	Synchronous Reset Setup Time	0.233	–	ns
tsrsthd	Synchronous Reset Hold Time	0.037	–	ns
twesu	Write Enable Setup Time	0.402	–	ns
twehd	Write Enable Hold Time	0.25	–	ns
Fmax	Maximum Frequency	–	300	MHz

Table 120 • RAM1K18 – Dual-Port Mode for Depth × Width Configuration 2Kx9
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Speed Grade –1		Units
		Min	Max	
tcy	Clock Period	3.333	–	ns
tclkmpwh	Clock Minimum Pulse Width High	1.5	–	ns
tclkmpwl	Clock Minimum pulse Width Low	1.5	–	ns
tplcy	Pipelined Clock Period	3.333	–	ns
tplclkmpwh	Pipelined Clock Minimum Pulse Width High	1.5	–	ns
tplclkmpwl	Pipelined Clock Minimum pulse Width Low	1.5	–	ns
tclk2q	Read Access Time with Pipeline Register	–	0.346	ns
	Read Access Time without Pipeline Register	–	2.346	ns
	Access Time with Feed-Through Write Timing	–	1.578	ns
taddrsu	Address Setup Time	0.49	–	ns
taddrhd	Address Hold Time	0.282	–	ns
tdsu	Data Setup Time	0.346	–	ns
tdhd	Data Hold Time	0.084	–	ns
tblksu	Block Select Setup Time	0.214	–	ns
tblkhd	Block Select Hold Time	0.223	–	ns
tblk2q	Block Select to Out Disable Time (when Pipe-Lined Registered is Disabled)	–	1.578	ns
tblkmpw	Block Select Minimum Pulse Width	0.218	–	ns
trdesu	Read Enable Setup Time	0.5	–	ns
trdehd	Read Enable Hold Time	0.073	–	ns
trdplesu	Pipelined Read Enable Setup Time (A_DOUT_EN, B_DOUT_EN)	0.256	–	ns
trdplehd	Pipelined Read Enable Hold Time (A_DOUT_EN, B_DOUT_EN)	0.106	–	ns
tr2q	Asynchronous Reset to Output Propagation Delay	–	1.569	ns

Table 128 • uSRAM (RAM128x8) in 128x8 Mode
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V (continued)

Parameter	Description	Speed Grade –1		Units
		Min	Max	
tr2q	Read Asynchronous Reset to Output Propagation Delay (With Pipe-Line Register Enabled)	–	0.865	ns
tsrstsu	Read Synchronous Reset Setup Time	0.279	–	ns
tsrsthd	Read Synchronous Reset Hold Time	0.062	–	ns
tccy	Write Clock Period	4	–	ns
tcclkmpwh	Write Clock Minimum Pulse Width High	1.8	–	ns
tcclkmpwl	Write Clock Minimum Pulse Width Low	1.8	–	ns
tblkcsu	Write Block Setup Time	0.417	–	ns
tblkchd	Write Block Hold Time	0.007	–	ns
tdincsu	Write Input Data setup Time	0.104	–	ns
tdinchd	Write Input Data hold Time	0.142	–	ns
taddrcsu	Write Address Setup Time	0.091	–	ns
taddrchd	Write Address Hold Time	0.24	–	ns
twecsu	Write Enable Setup Time	0.41	–	ns
twechd	Write Enable Hold Time	-0.027	–	ns
fmax	Maximum Frequency	–	250	MHz

Table 129 • uSRAM (RAM256x4) in 256x4 Mode
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Speed Grade –1		Units
		Min	Max	
tcy	Read Clock Period	4	–	ns
tclkmpwh	Read Clock Minimum Pulse Width High	1.8	–	ns
tclkmpwl	Read Clock Minimum pulse Width Low	1.8	–	ns
tplcy	Read Pipe-line clock period	4	–	ns
tplclkmpwh	Read Pipe-line clock Minimum Pulse Width High	1.8	–	ns
tplclkmpwl	Read Pipe-line clock Minimum Pulse Width Low	1.8	–	ns
tclk2q	Read Access Time with Pipeline Register	–	0.276	ns
	Read Access Time without Pipeline Register	–	1.812	ns
taddrsu	Read Address Setup Time in Synchronous Mode	0.311	–	ns
	Read Address Setup Time in Asynchronous Mode	1.993	–	ns
taddrhd	Read Address Hold Time in Synchronous Mode	0.125	–	ns
	Read Address Hold Time in Asynchronous Mode	-0.669	–	ns
trdensu	Read Enable Setup Time	0.287	–	ns

Table 136 • **Electrical Characteristics of the Crystal Oscillator – Low Gain Mode (32 kHz)**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Min	Typ	Max	Units
IDYNXTAL	Operating current	–	0.044	–	mA
VIHXTAL	Input logic level High	0.9 × VPP	–	–	V
VILXTAL	Input logic level Low	–	–	0.1 × VPP	V
SUXTAL	Startup time (with regard to stable oscillator output)	–	–	120	ms

14. On-Chip Oscillator

Table 137 and Table 138 describe the electrical characteristics of the available on-chip oscillators in the IGLOO2 FPGAs and SmartFusion2 SoC FPGAs.

Table 137 • **Electrical Characteristics of the 50 MHz RC Oscillator**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Condition	Min	Typ	Max	Units
F50RC	Operating frequency	–	–	50	–	MHz
ACC50RC	Accuracy	–	–	1	8	%
CYC50RC	Output duty cycle	–	–	49–51	46–54	%
JIT50RC	Output jitter (peak to peak)	Period Jitter	–	200	500	ps
		Cycle-to-Cycle Jitter	–	320	900	ps
IDYN50RC	Operating current	–	–	8.5	–	mA

Table 138 • **Electrical Characteristics of the 1 MHz RC Oscillator**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Condition	Min	Typ	Max	Units
F1RC	Operating frequency	–	–	1	–	MHz
ACC1RC	Accuracy	–	–	1	6	%
CYC1RC	Output duty cycle	–	–	49–51	46.5–53.5	%
JIT1RC	Output jitter (peak to peak)	Period Jitter	–	10	36	ps
		Cycle-to-Cycle Jitter	–	10	50	ps
IDYN1RC	Operating current	–	–	0.1	–	mA
SU1RC	Startup time	–	–	–	20	µs

21. DDR Memory Interface Characteristics

Table 150 • **DDR Memory Interface Characteristics**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Standard	Supported Data Rate			Unit
	Min	Typ	Max	
DDR3		667		Mbps
DDR2		667		Mbps
LPDDR	50	–	400	Mbps

25. CAN Controller Characteristics

Table 161 • **CAN Controller Characteristics**
Worst-Case Military Conditions: T_J = 125°C, VDD = 1.14 V

Parameter	Description	Min	Typ	Max	Units	Notes
FCANREFCLK	Internally Sourced CAN Reference Clock Frequency	–	–	128	MHz	*
BAUDCAN	CAN Performance Baud Rate	0.05	–	1	Mbps	–
Note: PCLK to CAN controller must be a multiple of 8 MHz.						